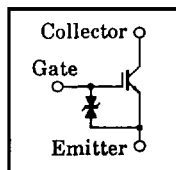


GT8G101

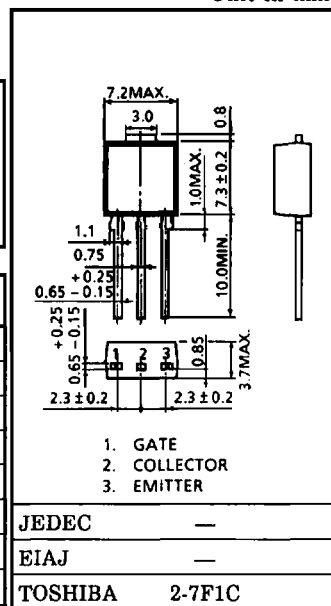
SILICON N CHANNEL MOS TYPE

STROBE FLASH APPLICATIONS

- Enhancement-Mode
- Low Saturation Voltage
: $V_{CE(sat)} = 8V$ (Max.) (@ $I_C = 130A$)
- 4.3V Gate Drive



Unit in mm



Weight : 0.72g

MAXIMUM RATINGS ($T_a = 25^\circ C$)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Emitter Voltage	V_{CES}	400	V
Gate-Emitter Voltage	DC	V_{GES}	± 6 V
	Pulse	V_{GES}	± 8 V
Collector Current	DC	I_C	8 A
	1ms	I_{CP}	130 A
Collector Power Dissipation	$T_a = 25^\circ C$	P_C	1.3 W
	$T_c = 25^\circ C$	P_C	20 W
Junction Temperature	T_j	150	$^\circ C$
Storage Temperature Range	T_{stg}	$-55 \sim 150$	$^\circ C$

ELECTRICAL CHARACTERISTICS ($T_a = 25^\circ C$)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Gate Leakage Current	I_{GES}	$V_{GE} = \pm 6V, V_{CE} = 0$	—	—	± 10	μA
Collector Cut-off Current	I_{CES}	$V_{CE} = 400V, V_{GE} = 0$	—	—	10	μA
Gate-Emitter Cut-off Voltage	$V_{GE(off)}$	$I_C = 1mA, V_{CE} = 5V$	0.5	—	1.2	V
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 130A, V_{GE} = 4.3V$	—	5	8	V
Input Capacitance	C_{ies}	$V_{CE} = 10V, V_{GE} = 0, f = 1MHz$	—	1900	—	pF
Switching Time	Rise Time		—	0.9	—	μs
	Turn-on Time		—	1.1	—	
	Fall Time		—	2.0	—	
	Turn-off Time		—	2.4	—	
Thermal Resistance	$R_{th(j-c)}$	—	—	—	6.25	$^\circ C/W$